



EPITAXIAL-BASE NPN/PNP

POWER DARLINGTONS

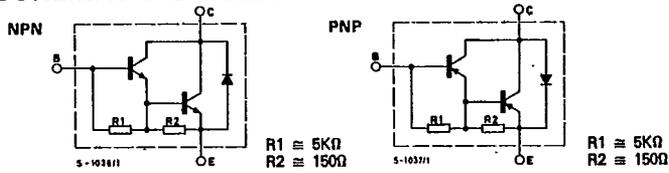
The SGS120, SGS121 and SGS122 are silicon epitaxial-base NPN transistors in monolithic Darlington configuration in SOT-82 plastic package intended for use in power linear and switching applications.

The complementary PNP type are the SGS125, SGS126 and SGS127 respectively.

ABSOLUTE MAXIMUM RATINGS		NPN PNP	SGS120 SGS125	SGS121 SGS126	SGS122 SGS127
V_{CBO}	Collector-base voltage ($I_E=0$)		60V	80V	100V
V_{CEO}	Collector-emitter voltage ($I_B=0$)		60V	80V	100V
V_{EBO}	Emitter-base voltage ($I_C=0$)			5V	
I_C	Collector current			5A	
I_{CM}	Collector peak current			8A	
I_B	Base current			0.1A	
P_{tot}	Total power dissipation at $T_{case} \leq 25^\circ C$ $T_{amb} \leq 25^\circ C$			65W	
T_{stg}	Storage temperature			-65 to 150°C	
T_j	Junction temperature			150°C	

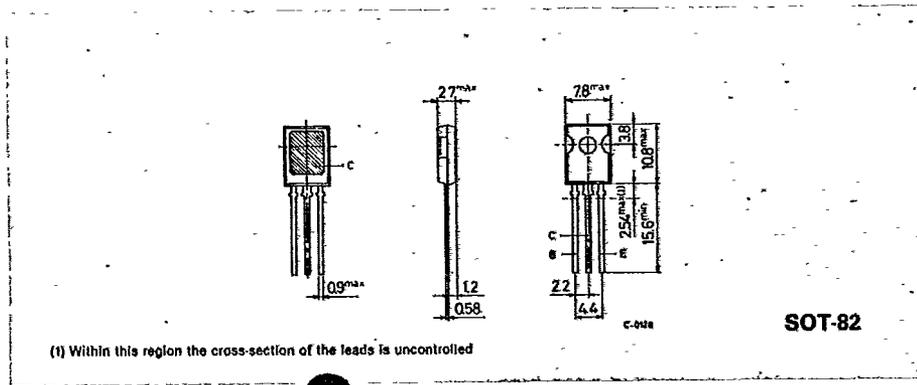
For PNP types voltage and current values are negative.

INTERNAL SCHEMATIC DIAGRAMS



MECHANICAL DATA

Dimensions in mm





THERMAL DATA

$R_{th\ j-case}$	Thermal resistance junction-case	max	1.92	°C/W
$R_{th\ j-amb}$	Thermal resistance junction-ambient	max	62.5	°C/W

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CEO}	Collector cutoff current ($I_B = 0$)			0.5	mA
I_{CBO}	Collector cutoff current ($I_E = 0$)			0.2	mA
I_{EBO}	Emitter cutoff current ($I_C = 0$)			2	mA
$V_{CE(sus)}^*$	Collector-emitter sustaining voltage ($I_B = 0$)			60 80 100	V V V
$V_{CE(sat)}^*$	Collector-emitter saturation voltage	$I_C = 3A$ $I_C = 5A$	$I_B = 12mA$ $I_B = 20mA$	2 4	V V
V_{BE}^*	Base-emitter voltage	$I_C = 3A$	$V_{CE} = 3V$	2.5	V
h_{FE}^*	DC current gain	$I_C = 0.5A$ $I_C = 3A$	$V_{CE} = 3V$ $V_{CE} = 3V$	1000 1000	— —

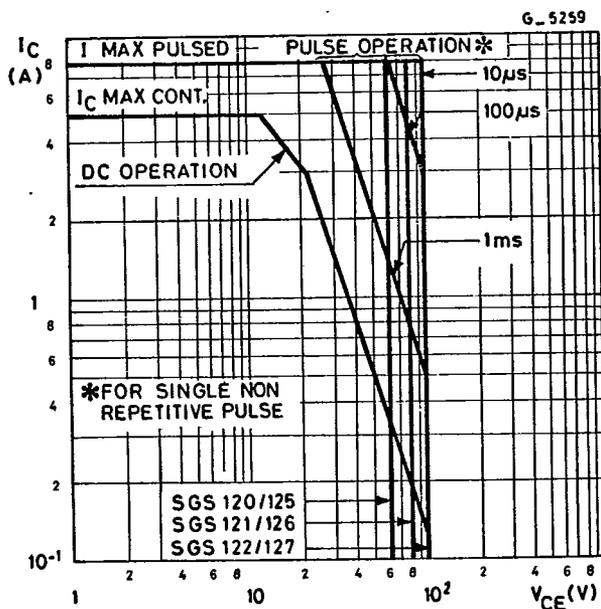
* Pulsed: pulse duration = 300 μ s, duty cycle \leq 2%.

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SGS120 SGS125
SGS121 SGS126
SGS122 SGS127

Safe operating areas



For the others characteristics curves see BDX33/BDX34 series